

DMG3402L

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

BVDSS	Rds(on)	I _D T _A = +25°C
	52mΩ @ V _{GS} = 10V	4A
30V	65mΩ @ V _{GS} = 4.5V	3A
	85mΩ @ V _{GS} = 2.5V	2A

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

 An automotive-compliant part is available under separate datasheet (<u>DMG3402LQ</u>)

Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

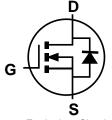
Applications

- DC-DC converters
- Power-management functions
- Battery operated systems and solid-state relays

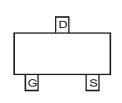
SOT23 (Standard)







Equivalent Circuit



Pin Configuration

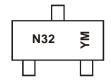
Ordering Information (Note 4)

Part Number	Dookono	Pa	Packing		
Part Number	Package	Qty.	Carrier		
DMG3402L-7	SOT23 (Standard)	3000	Tape & Reel		
DMG3402L-13	SOT23 (Standard)	10000	Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



N32 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: K = 2023) M = Month (ex: 9 = September)

Date Code Key

Date Code Rey												
Year	2013		2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	Α		K	L	М	N	Р	R	S	T	U	V
Month	lan	Feb	Mar	Anr	May	lun	lul	Aug	Sep	Oct	Nov	Dec
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	VDSS	30	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 5)	ID	4.0	А
Body-Diode Continuous Current (Note 5)	Is	1.5	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	Po	1.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	Reja	90	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

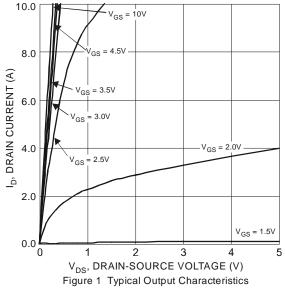
Electrical Characteristics (@ TA = +25°C, unless otherwise specified.)

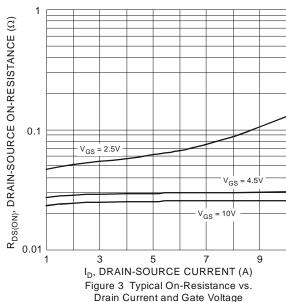
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)								
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	V _G S = 0V, I _D = 250μA		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$		
Gate-Body Leakage	lgss	_	_	±100	nA	Vgs = ±12V, Vps = 0V		
ON CHARACTERISTICS (Note 6)	, ,							
Gate Threshold Voltage	Vgs(TH)	0.6	_	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$		
			_	52		$V_{GS} = 10V, I_D = 4A$		
Static Drain-Source On-Resistance	RDS(ON)	_	_	65	mΩ	$V_{GS} = 4.5V, I_{D} = 3A$		
			_	85		$V_{GS} = 2.5V, I_{D} = 2A$		
Forward Transconductance	Yfs	_	6.6	_	S	$V_{DS} = 5V, I_{D} = 3.1A$		
Source-Drain Diode Forward Voltage	V _{SD}	_	_	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$		
DYNAMIC CHARACTERISTICS (Note 7)								
Gate Resistance	Rg	_	2.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge (10V)	Qg	_	11.7	_	nC	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 4A$		
Total Gate Charge (4.5V)	Qg	_	5.5	_	nC			
Gate-Source Charge	Qgs	_	1.1	_	nC	$V_{GS} = 10V, V_{DS} = 15V,$		
Gate-Drain Charge	Qgd	_	1.8	_	nC	I _D = 4A		
Turn-On Delay Time	tD(ON)	_	1.9	_	ns			
Turn-On Rise Time	tR	_	1.6	_	ns	V _{DD} = 15V, V _{GEN} = 10V,		
Turn-Off Delay Time	t _{D(OFF)}	_	10.3	_	ns	$R_{GEN} = 3\Omega$, $R_L = 3.75\Omega$		
Turn-Off Fall Time	tF	_	2.0		ns			
Input Capacitance	Ciss	_	464	_	pF			
Output Capacitance	Coss	_	49.5	_	pF	V _{DS} = 15V, V _{GS} = 0V		
Reverse Transfer Capacitance	C _{rss}	_	43.8	_	pF	f = 1.0MHz		

Notes: $5. \ \, \text{Device mounted on FR-4 PCB.} \ t \leq 5 \text{sec, 2oz copper 1} \\ \text{inch FR-4 board with minimum recommend pad layout.} \\$

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







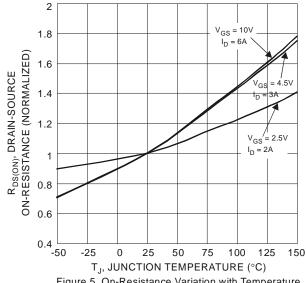
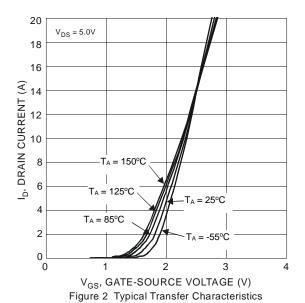
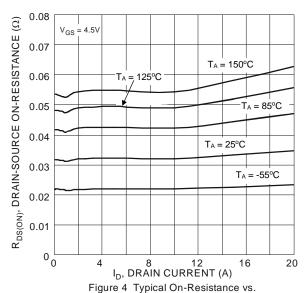


Figure 5 On-Resistance Variation with Temperature





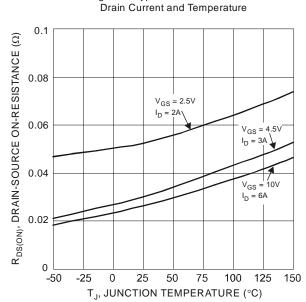


Figure 6 On-Resistance Variation with Temperature



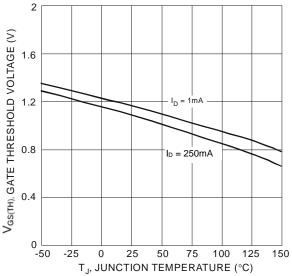
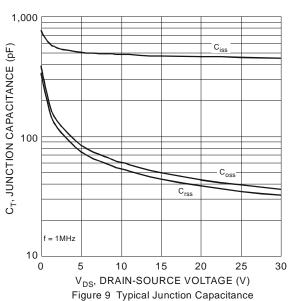
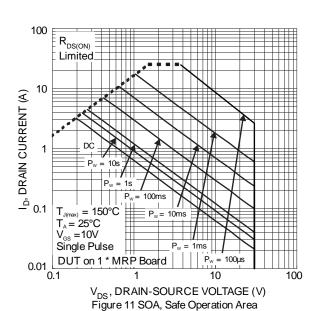


Figure 7 Gate Threshold Variation vs. Ambient Temperature





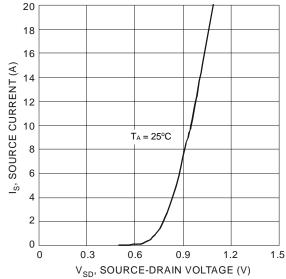
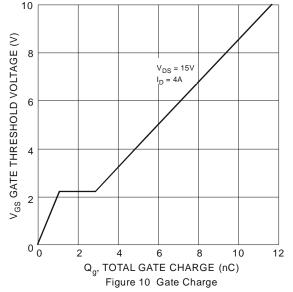
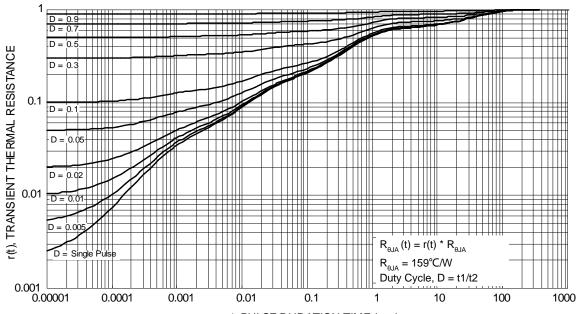


Figure 8 Diode Forward Voltage vs. Current







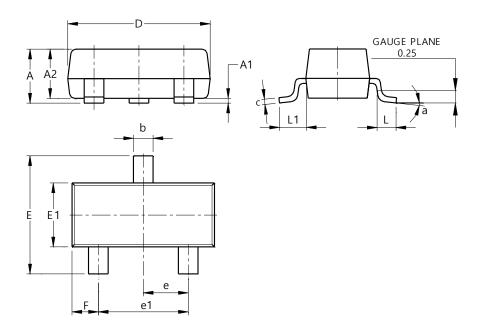
t1, PULSE DURATION TIME (sec) Figure 12 Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

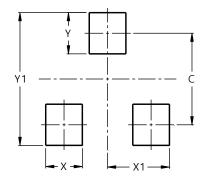
SOT23 (Standard)



SOT23 (Standard)							
Dim	Min	Max	Тур				
Α	0.90	1.15	1.025				
A1	0.00	0.10	0.05				
A2	0.85	1.10	0.975				
b	0.30	0.51	0.40				
С	0.080	0.202	0.11				
D	2.80	3.00	2.90				
Е	2.25	2.55	2.40				
E1	1.20	1.40	1.30				
е	0.89	1.03	0.915				
e1	1.78	2.05	1.83				
F	0.40	0.60	0.535				
L1	0.45	0.61	0.55				
L	0.25	0.55	0.40				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

SOT23 (Standard)



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Y	0.9
Y1	29



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